

Proton Irradiation Experiment for the X-ray Charge-Coupled Devices of the Monitor of All-sky X-ray Image mission onboard the International Space Station: I. Experimental Setup and Measurement of the Charge Transfer Inefficiency

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We have investigated the radiation damage effects on a CCD to be employed in the Japanese X-ray astronomy mission including the Monitor of All-sky X-ray Image (MAXI) onboard the International Space Station (ISS). Since low energy protons release their energy mainly at the charge transfer channel, resulting a decrease of the charge transfer efficiency, we thus focused on the low energy protons in our experiments. A 171 keV to 3.91 MeV proton beam was irradiated to a given device. We measured the degradation of the charge transfer inefficiency (CTI) as a function of incremental fluence. A 292 keV proton beam degraded the CTI most seriously. Taking into account the proton energy dependence of the CTI, we confirmed that the transfer channel has the lowest radiation tolerance. We have also developed the different device architectures to reduce the radiation damage in orbit. Among them, the “notch” CCD, in which the buried channel implant concentration is increased, resulting in a deeper potential well than outside, has three times higher radiation tolerance than that of the normal CCD. We then estimated the charge transfer inefficiency of the CCD in the orbit of ISS, considering the proton

energy spectrum. The CTI value is estimated to be 1.1×10^{-5} per each transfer after two years of mission life in the worse case analysis if the highest radiation-tolerant device is employed. This value is well within the acceptable limit and we have confirmed the high radiation-tolerance of CCDs for the MAXI mission.

KEYWORDS: charge-coupled device, radiation damage, displacement, international space station, radiation belt

1. Introduction

Charge-coupled devices (CCDs) have emerged as the preferred detectors on all new X-ray astronomy mission in recent years. This is because they possess a high spatial resolution as well as a moderate energy resolution, simultaneously.¹⁾ The dead layer above CCD must be thin enough to attain a high quantum efficiency at soft X-ray regions. As the result, devices cannot be protected against the high energy particles in space in the incident direction of X-rays.

Soon after the launch of the X-ray astronomy satellite, *Chandra*, all of the front-illuminated CCD of the X-ray CCD camera (ACIS) have suffered some damage caused by the charge transfer inefficiency (CTI).²⁾ The CTI is defined as an average fraction of charge packet lost at each transfer. Similar type of devices to ACIS CCDs have been tested by the high energy protons (40 MeV and 10 MeV) but not by the low energy protons before launch. The low energy protons having energy of ~ 150 keV release major part of its energy at the transfer channel of the ACIS CCDs, which is located roughly $1\text{ }\mu\text{m}$ below the electrodes. They cause the displacement damages in Si, leading to the formation of trapping sites for the charge packet. Since the flux of low energy protons at the orbit of *Chandra* is much higher than that at the low earth orbit such as ASCA³⁾ and low energy protons reflecting through the X-ray mirror assembly (HRMA) can reach the focal plane,⁴⁾ a significant degradation of the CTI has occurred.

The Monitor of All-sky X-ray Image (MAXI) has been selected as an early payload of the JEM (Japanese Experimental Module; *KIBO*) Exposed Facility on the International Space Station (ISS).⁵⁾ MAXI has slit scanning cameras which consist of two kinds of X-ray detectors; one-dimensional position sensitive proportional counters with total area of $\sim 5000\text{ cm}^2$ named GSC and the X-ray CCD camera with total area of $\sim 200\text{ cm}^2$ named SSC. SSC carries 32 CCDs which are three-side buttable with full-frame transfer and have 1024×1024 pixels of $24\text{ }\mu\text{m} \times 24\text{ }\mu\text{m}$ size with two phase gate structures. The CCD chips are fabricated by the Hamamatsu Photonics K. K. (HPK). In order to perform useful X-ray spectroscopy over the whole device, the CTI must be less than roughly 2×10^{-5} per transfer where the shift of the peak energy is similar to that of the Fano-limited noise

of 120 eV at 5.9 keV.

Previous studies of the radiation hardness for HPK CCDs were also focused on high energy protons above 1 MeV⁶⁾ and no data are available for low energy protons. We thus performed the irradiation test focusing on the low energy protons. In this paper, we describe the device architecture, irradiation experiment, and the measurement of the CTI at -100°C .

2. Experiments and Results

2.1 Architecture of CCD

We employed CCDs packaged in a half-inch size which is different from that of the MAXI CCD whereas the device was fabricated from the same type of wafer of the MAXI CCD. The devices irradiated possess 512×512 pixels of which size is $24\text{ }\mu\text{m}$ square. Figure 1(a) shows the schematic view of the CCD. The cross section of a CCD pixel in the horizontal and the vertical direction is shown in Fig 1(b) (we call this type of device as normal CCD which has no countermeasure for radiation hardness). Since the CCD employed is a buried-channel type, there is a thin ($\simeq 1\text{ }\mu\text{m}$) doped n -type layer just below the oxide layer. There are four electrodes per pixel in our case and they slightly overlap each other as shown in the cross section of Fig 1(b) (*right*). There is another gate structure, a “channel stop”, which forms the pixel boundary along the vertical transfer direction shown in Fig 1(b) (*left*).

We need to develop a highly radiation-tolerant device to be employed in space for a long time. One of the design to improve the radiation tolerance is a “notch” structure.⁷⁾ The notch CCD incorporated a narrow, $\sim 3\text{ }\mu\text{m}$, strip both for vertical and horizontal registers in which the buried channel implant concentration was increased, resulting in a deeper potential well than outside the notch structure as shown in bottom of Fig 1(c). Small charge packet would be confined within the notch structure to reduce the probability to encounter with vacant traps by a factor of ~ 8 . We therefore expect that the CTI would be improved in the device having the notch structure as CRAF/Cassini CCDs⁷⁾ and EEV CCDs.⁸⁾ We should note that all devices used in section 2.3 and 2.4 possesses the notch structure.

Another technique employed is to replace some amount of the Si oxide with the nitride oxide as shown in Fig 1(d) (nitride CCD, hereafter). The thickness of the oxide layer and the nitride layer of the nitride CCD we fabricated is similar to that of the oxide layer of the normal device. There is no differences below and above the nitride and oxide layer between the nitride CCD and the normal CCD. The nitridation of the oxide layer enables us to reduce the ionization damage, resulting the effect of the flat-band shift to be smaller than those of devices having only oxides.^{9,10)} This technique would reduce the dark current for damaged devices. It might not be efficient to improve the CTI since the nitride CCD possesses the similar structure of the depletion layer to the normal CCD. However, the degradation of the CTI must be similar level for normal devices.

We have developed CCDs from various Si wafers. Details about newly-developed devices have been described in Miyata *et al.*¹¹⁾ Devices fabricating from epitaxial wafer and from bulk wafer were tested. We have decided to employ devices from epitaxial wafer in order to achieve the high energy resolution, high quantum efficiency for hard X-rays, and also low dark current. Among them, we employed the epitaxial-2 (hereafter referred as epi-2) and epitaxial-3 (referred as epi-3) devices for comparison. The resistivity of epi-3 wafer is roughly an order of magnitude higher than that of epi-2 wafer.

We then fabricated following four types devices to compare their radiation tolerance; epi-3 with and without notch, epi-2 with notch, and epi-2 without notch but having the nitride oxide.

2.2 *Experimental setup and beam calibration*

A 570 keV to 4.0 MeV proton beam, shown in Table I, was provided by the Van de Graaff accelerator at the Laboratory for Nuclear Studies, Osaka University. We employed an Al degrader with a thickness of $5\text{ }\mu\text{m}$ to reduce the energy down to 171 keV (Table I). Pulsed beams were used to control the irradiation fluence. The proton beam was over-defocussed by quadrupole magnet to obtain a weak and uniform beam at the CCD.

Figure 2 shows the experimental setup of the CCD chamber. We employed four diaphragm plates made of Al between the degrader and the CCD in order to reduce scattered protons or secondary electrons generated by the inside wall of the duct. Inside

the CCD chamber, the collimator made of Al with a thickness of 3 mm having a hole of 21 mm ϕ was set both to collimate the proton beam and to monitor the intensity of the incident proton beam to the CCD. Two ^{55}Fe sources were located behind the collimator. It enabled us to investigate the *in-situ* performance of the CCD.

Roughly a half area of each CCD was shielded against protons to provide the non-irradiated data to compare with those from the irradiated region. Since the amount of scattering of protons is not small, the vertical boundary between the shielded and the irradiated region was not so clear. It makes the calculation of the CTI in the horizontal transfer direction to be much uncertain. We thus focused on the vertical CTI only.

We drove CCDs with our newly-developed system, *E-NA* system.¹²⁾ The CCD analog data were processed by an integration-type circuit¹¹⁾ and digital data were acquired with a VME system. The readout noise of our system including the device is less than 10 e^- rms under the charge transfer rate of 125 kHz.

We calibrated the beam current with replacing the CCD by a Faraday cup made of Al shown in Fig 2. We measured the current at the Faraday cup and the collimator with pico-ammeter, simultaneously. We thus obtained the ratio of each current at given energy. We found that the ratio depended on the beam energy possibly because the probability of secondary emission depends on the beam energy when protons hit materials inside the chamber. The accuracy of the beam intensity estimated from the collimator current could be achieved to be 5 % taking into account their energy dependence.

The spatial uniformity of the beam intensity was measured with 650 keV protons. The proton energy at downstream of the degrader was 292 keV (detail will be described in the next section). A 292 keV proton generate electron-hole pair along its track inside the CCD. Electrons generated only at the depletion layer can be collected. After passing through the covering layer, electrode, and the oxide layer shown in Fig 1(b), the proton energy was reduced to be $\sim 6\text{ keV}$ which generate charge cloud consisting of $\sim 1.6 \times 10^3$ electrons, which is much lower than the capacity of a pixel. We, therefore, irradiated very weak 650 keV proton beam onto the CCD so that pile-up effect is negligibly small. Protons detected by CCDs formed various types of events similar to X-rays: single-pixel event, two-pixel split event, and more extended event. We thus measured the number

of events generated by protons in 24 mm squares and found the spatial uniformity to be better than 10 %.

2.3 Performance degradation of mono-energetic protons

We performed the incremental irradiations at given energy on a given device. All devices were in operation (biased) during this experiment and fabricated from the same wafer (epitaxial-3 wafer). Table I shows the energy of proton irradiated. The center energy and width of proton spectrum at downstream of the degrader were calculated with the *Geant4*.¹³⁾ We employed the low energy extension with *G4EMLOW0.3* data in *Geant4* in order to simulate the physical process of low energy less than 2 MeV.¹⁴⁾ In the subsequent section, we only referred the proton energy to that at downstream of the degrader.

Figure 3 (a) shows the spectrum of ^{55}Fe extracted from single-pixel events before proton irradiation. The energy resolution of Mn $K\alpha$ has a full-width at a half maximum (FWHM) of 146 eV. After an irradiation of 292 keV proton with a fluence of $1.04 \times 10^7 \text{ cm}^{-2}$, the degradation of the detector performance was significant and the energy resolution became 294 eV (Fig 3 (b)). The peak positions of Mn $K\alpha$ and $K\beta$ were shifted, suggesting the incomplete collection of the charge packet. We then incremented fluence up to $1.11 \times 10^8 \text{ cm}^{-2}$ and resultant spectrum is shown in Fig 3 (c). Mn $K\alpha$ and $K\beta$ X-rays could not be resolved and the energy resolution was degraded to 614 eV. The device irradiated with 292 keV protons suffered the most serious damage on the energy resolution compared with those irradiated by protons of other energies.

Figure 4 shows the readout noise as a function of proton fluence for 292 keV and 3.91 MeV protons. Since the readout noise was evaluated from the histogram of the horizontal over-clocked area, it included the noise of CCD as well as that of the electronics. Before the proton irradiation, the readout noise of both CCDs were $\sim 7.8 \text{ e}^-$. Therefore, there was not an influence of proton irradiations on the readout noise. In this way, we confirmed no degradation of the readout noise for irradiations with protons of any energies employed. The degradation of energy resolution shown in Fig 3 was not caused by the degradation of the readout noise.

Figure 5 shows the pulse heights of ^{55}Fe events as a function of the number of transfer. Each dot in these figures corresponds to an individual X-ray event. The histogram shown in Fig 3 can be obtained if one makes a projection of these plots to Y-axis (pulse height axis). Before irradiation, there are two horizontal lines clearly seen, corresponding to Mn $K\alpha$ at ~ 710 channel and $K\beta$ at ~ 790 channel (Fig 5 (a)). After irradiating with 292 keV protons with fluence of $1.04 \times 10^7 \text{ cm}^{-2}$, the pulse height of X-ray events decreases with increasing transfer number, suggesting the loss of the charge packet during the transfer (Fig 5 (b)). We should note that the widths of two lines were broadened as the transfer number became larger. Figure 5 (c) shows the same plot after irradiating with protons of $1.11 \times 10^8 \text{ cm}^{-2}$. The significant loss of charge packet is found and the pulse height at the transfer number of 500 is less than half of that before irradiation. The pulse height at the transfer number of zero is still less than that before irradiation, suggesting the loss of charge packet in the serial register of the device.

In order to characterize the loss of charge packet, we calculated the values of the CTI for all proton energies based on Fig 5. Figure 6 shows the CTI as a function of proton fluence for various proton energies. Protons having energy of 150 keV have seriously degraded the detector performance in the case of ACIS. On the other hand, 171 keV protons affected the CTI for HPK CCDs less effectively. Instead, HPK CCDs suffered serious damage by protons with higher energies of 292 and 391 keV. The degradation of the CTI caused by proton energies above 500 keV is again less than those of protons of 292 and 391 keV.

Since values of the CTI shown in Fig 6 depend on the initial value of the CTI, we calculated the increase rate of the CTI (ΔCTI) as a function of proton fluence at each incremental irradiation for various energies, shown in Fig 7.

2.4 Dependence of CTI on biased and unbiased devices

On the satellite orbit including the ISS, high energy particles distribute far from uniform but concentrate in a very small area on the Earth. The most dense region of the high energy particles is so-called the South Atlantic Anomaly (SAA). During the passage of the SAA, the quality of data would be bad because of high background. Therefore, if the performance degradation of CCDs depends on the biased (in operation) or unbiased (out

of operation) condition, we could turn off CCDs during the passage of the SAA.

We thus investigated the difference of device performance whether the device was biased or not during irradiation of 292 keV protons. Figure 8 shows the ΔCTI as a function of proton fluence. We found no significant difference between them. Therefore, the devices need not to be turned off during SAA only taking into account the degradation of CTI.

2.5 CTI for various devices and for various processes

As written in section 2.1, we fabricated four types devices to compare the difference of radiation hardness. All devices were unbiased during the proton irradiation. The values of ΔCTI obtained for these devices are shown in Fig 9. We found that ΔCTI value obtained by epi-3 with notch is factor of 3 – 5 times lower than that with epi-3 without notch. Significant improvement is obtained although this value is slightly smaller than that of the geometrical ratio of notched area and other area. We thus decided to employ the notch structure for flight devices.

There is no significant difference between epi-2 with notch and epi-3 with notch, suggesting no differences in ΔCTI for high and low resistivity wafers. We can therefore investigate the effect of the nitride oxide comparing between epi-3 without notch and epi-2 without notch but having the nitride oxide. There were very little differences between. Therefore, if the degradation of the dark current in the device having the nitride oxide is smaller than that without the nitride oxide, we will employ the nitride oxide for flight devices. The experimental results concerning about the dark current is described in the subsequent paper.

3. Discussion

3.1 Proton Bragg curve

We found that protons having energies of 292 and 391 keV seriously damaged HPK CCDs on the CTI performance. The degradation of the CTI obtained with protons having lower and higher energies is much less than those with 292 and 391 keV protons. This strongly suggests that the low radiation-tolerant region inside the HPK CCD is located in relatively a narrow region.

We calculated the Bragg curves of protons in Si. We employed *Geant4* with the

G4EMLOW0.3 data and considered the energy straggling due to the Al degrader of $5\mu\text{m}$ in thickness. Figure 10 (*upper*) shows the energy loss of protons as a function of depth of Si. The dotted line represents the minimum energy to displace Si atoms ($\simeq 6\text{ eV } \text{\AA}^{-1}$).¹⁵⁾ The energy deposition due to 292 and 391 keV protons are concentrated at the depth of $2 - 4\mu\text{m}$ inside Si. In this depth, the energy deposition of protons with other energies is less than those of 292 and 391 keV. Therefore, the radiation tolerance at depth of $2 - 4\mu\text{m}$ is much lower than those in other region inside the HPK CCD.

Figure 10 (*lower*) shows the schematic view of the cross section of the HPK CCD employed. Since the HPK CCD is a buried-channel type, the charge packet is transferred in a narrow region along the depth of the CCD. This transfer channel well coincides with the Bragg peak region. We thus conclude that the transfer channel of the CCD possesses the lowest radiation tolerance for protons. This result is consistent with the ACIS result but the serious proton energy is slightly different from our value. Prigozhin *et al.*²⁾ estimated the minimum proton energy to reach the buried channel to be somewhat higher than 50–70 keV in order to penetrate the optical blocking filter, covering layer, and electrodes. Therefore, the thickness of the covering material is much thinner than our case, resulting that lower energy protons seriously affected the ACIS CCDs.

As described in section 2.5, there is no difference in CTI values between CCDs fabricating from high resistivity wafer and those from low resistivity wafer. The acceptor doping concentration of our device is only an order of $10^{13} - 10^{14}\text{ cm}^{-3}$ and the difference between epi-2 wafer and epi-3 wafer is roughly an order of magnitude.¹¹⁾ Therefore, the probability that protons encounter Si atom is essentially the same between these devices. Since the thickness of *n*-type layer is the same between them, their difference is the thickness of a depletion layer. It means that the location of the transfer channel is at the same depth between them. Our results are, therefore, expected if the radiation tolerance depends not on the depletion depth but on the transfer channel. This is consistent with the previous work.⁸⁾ We are now developing CCDs from newly-obtained epitaxial wafer having much higher resistivity than that of epi-3. Since, however, the location of the transfer channel of new CCDs is the same depth as current devices, we are convinced that we can apply these results to new CCDs.

3.2 Modeling the CTI degradation

As shown in Fig 7, the degradations of ΔCTI are expressed as a linear function of the proton fluence. Since ΔCTI is expressed as a linear function of the electron trap density,¹⁶⁾ the formation of electron traps proportionally corresponds to proton fluence. Values of ΔCTI are fitted to a linear function of proton fluence. The best fit parameters, a slope and an intercept (ΔCTI_0), are shown in Table II. Figure 11 shows the slope obtained as a function of proton energy. Since the obtained values of slope correspond to an efficiency to create the electron trap, Fig 11 shows that 292 keV protons most seriously affect the CTI degradation.

As shown in Fig 10, low energy protons deposit major part of their energy within a confined depth. The peak of the Bragg curve corresponds to the depth of $2.3\text{ }\mu\text{m}$ in Si in the case of 292 keV protons. We thus assume there is a thin radiation-sensitive area within the CCD at depth of $2.3\text{ }\mu\text{m}$ with thickness of $0.05\text{ }\mu\text{m}$. We should note that $0.05\text{ }\mu\text{m}$ is the shortest unit we can simulate. Ignoring the ΔCTI degradation from other depths, we can calculate the energy deposition by protons that affect the CTI. Results are plotted in Fig 11 with filled circles normalized by value at 292 keV. For all proton energies, calculated values are much larger than those obtained. As shown in Fig 10, if the thickness of the radiation-sensitive region increases, the energy deposit of 391 or 522 keV protons becomes relatively larger than that of 292 keV protons. It drove the calculated values for 391 and 522 keV to be increased much more than current values, resulting the deviation from data to be more significant. In this calculation, we assumed that the probability to create an electron trap is linearly proportional to the proton energy loss. This assumption leads to a large discrepancies between the data and the calculations. Therefore, there may be some nonlinear effects in their probabilities.

There are two types of process for proton energy loss: an ionization energy loss (IEL) and a nonionization energy loss (NIEL). These two different forms of energy dissipation are translated into two major damage mechanisms for CCDs: an ionization damage and a bulk damage. The ionization damage leads to a flat-band shift which causes the operating voltage to be shifted. This damage is caused by all types of charged particles. On the other hand, energetic charged particles undergo Rutherford-scattering-type Coulombic

interactions with the Si lattice structure. The energy deposited by the interacting ion is enough to pull a silicon atom out of its lattice position, forming an interstitial Si atom and a vacancy. The displaced atom, called the primary knock-on atom (PKA), may have sufficient energy to undergo collisions with lattice, producing more vacancies. NIEL is responsible for a part of the energy producing the initial vacancy-interstitial pairs and phonons.

Ziegler *et al.*¹⁷⁾ and Burke¹⁸⁾ calculated the IEL and the NIEL, respectively. Based on their calculations, more than 98 % of incident proton energies (E_p [keV]) release as the IEL for $E_p \geq 100$ keV. For a proton of relativistic energies, the NIEL is almost constant whereas with lower energies the NIEL has a $1/E_p$ dependence. This suggests that the probability to create displacements is not linearly proportional to the total energy loss but is proportional to $E_p^{-\gamma}$. We then fitted the function $E_p^{-\gamma}$ to the results of NIEL calculated by Burke. We found that γ can be approximated to be $\simeq 0.76$ at the energy range of $100 \text{ keV} \leq E_p \leq 4 \text{ MeV}$.

In order to take into account the nonlinear effect in creating traps due to the NIEL, we need to employ not the incident proton energy but the energy at the depth of $2.3 \mu\text{m}$. We calculated the energy reduction of E_p during the passage of $2.3 \mu\text{m}$ in Si with *Geant4*. We then calculated the fraction of the NIEL among the total energy loss with taking into account of the energy dependence of the NIEL for each reduced E_p . We normalized the fraction of the NIEL for each proton energy by that of 292 keV and took them into account for the previous calculations. Results are shown by filled squares in Fig 11. Our calculations considering the NIEL represent the data obtained. However, values of slope measured suddenly decreases as E_p increases whereas they cannot be reproduced by our calculations. In our model, we only consider the NIEL which represent the energy deposition as the initial vacancy-interstitial pairs and phonons. If the energy of PKA is large enough to undergo collisions with Si atoms, the number of vacancies increase. Therefore, to take into account the spectrum of PKA and collisions between PKA and Si atoms is important for future modeling.

Empirical relations between the slope of the ΔCTI versus the proton energy are described as:

$$\text{slope}(E_p [\text{keV}]) = 1.2 \times 10^{-10} \times E_p - 2.0 \times 10^{-11} \quad \text{for } E_p \leq 292 \text{ keV} \quad (3.1)$$

$$\text{slope}(E_p [\text{keV}]) = 1.2 \times 10^{-9} \times \exp(-E_p/6.6 \times 10^{-2}) + 3.0 \times 10^{-13} \quad \text{for } E_p \geq 292 \text{ keV} \quad (3.2)$$

Solid lines in Fig 11 represent above empirical relations. For a given proton spectrum in orbit, we can calculate the ΔCTI value by summing contributions from all proton energies.

3.3 Estimate the CTI for the MAXI mission

We found that low energy protons with energies of 290 – 400 keV seriously damaged the spectroscopic performance of the MAXI CCDs. The degradation of CTI as a function of mission life for the MAXI based on our experiments has been estimated. There is a slit at the top of the SSC camera with a size of $5 \times 0.3 \text{ mm}^2$ and the slit collimators just above the CCDs.¹⁹⁾ The thickness of the slit collimator is $\sim 100 \mu\text{m}$, which is aligned by $\sim 3 \text{ mm}$ pitch, resulting the field of view of each CCD to be $\sim 1.5^\circ$ square. Within the field of view, no shield protects devices whereas the column density at other directions on the camera is $\sim 2.5 \text{ g cm}^{-2}$, suggesting the proton component passing through the camera to be negligibly small. We thus calculate the proton flux coming through $1.5^\circ \times 1.5^\circ$ area.

We employed the proton flux described in the literature,²⁰⁾ in which the attitude of the ISS is 500 km and solar activity is the maximum. The proton flux at 500 km is the largest among attitudes expected for the ISS²⁰⁾ and we therefore use it for the worst case analysis. The number of proton at the solar minimum is factor of ~ 2 larger than that at the solar maximum. We thus increase the proton flux with a factor of 1.5 as the average value. Figure 12 shows the CTI estimated for the MAXI as a function of its mission life. The dotted line shows the acceptable limit for the MAXI mission. Since the mission life of the MAXI is two years, the degradation of the CTI is well below the acceptable limit even for the worst case analysis. We therefore confirm the high radiation tolerance of MAXI CCDs.

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Figure captions

Fig. 1. (a) Schematic view of the CCD. (b) The cross section of a CCD pixel along the horizontal and the vertical direction is shown for the normal CCD. The horizontal cross section for (c) notch CCD and (d) nitride CCD is shown. The potential profile for electron is also shown in bottom of (c).

Fig. 2. Experimental setup of the proton irradiation test.

Fig. 3. Single-event spectra of ^{55}Fe sources for device (a) before irradiated, irradiated to (b) 1.04×10^7 and (c) 1.11×10^8 protons cm^{-2} having energy of 292 keV. All spectra were extracted from the same number of frames and taken at -100°C .

Fig. 4. Readout noise as a function of proton fluence for 292 keV and 3.91 MeV protons.

Fig. 5. Pulse height of ^{55}Fe events as a function of transfer number taken at -100°C for device (a) before irradiated, irradiated to (b) 1.04×10^7 and (c) 1.11×10^8 protons cm^{-2} having energy of 292 keV.

Fig. 6. CTI as a function of proton fluence for various proton energies.

Fig. 7. ΔCTI as a function of proton fluence for various proton energies.

Fig. 8. ΔCTI as a function of proton fluence for the device biased and unbiased during the proton irradiation.

Fig. 9. ΔCTI as a function of proton fluence for devices fabricating from various different wafer and different processes.

Fig. 10. Bragg curves for various proton energies (*upper*) and the schematic view of the cross section of HPK CCD employed (*lower*). The dotted line in the *upper* figure shows the minimum energy to displace Si atoms.

Fig. 11. Slope of ΔCTI as a function of proton energy. Model calculations with and without taking into account the nonlinear effect due to NIEL are also plotted by filled circles and filled squares, respectively. Solid lines represent the empirical relations.

Fig. 12. CTI estimated for the MAXI CCDs. The dotted line indicates the requirement for the MAXI.

Table I. Energy of proton irradiated.

upstream of the degrader	downstream of the degrader	
proton energy [keV]	proton energy [keV]	width [keV] ^a
570	171	13
650	292	12
720	391	11
820	522	11
2200	2061	10
4000	3911	9

^a Width is shown in unit of a standard deviation.

Table II. Result of linear fit for ΔCTI as a function of proton energy.

proton energy [keV]	slope	CTI_0
171	$(1.63 \pm 0.04) \times 10^{-13}$	$(5.3 \pm 0.9) \times 10^{-6}$
292	$(1.35 \pm 0.05) \times 10^{-11}$	$< 8 \times 10^{-6}$
391	$(3.34 \pm 0.03) \times 10^{-12}$	$(6.3 \pm 0.2) \times 10^{-5}$
522	$(1.10 \pm 0.01) \times 10^{-12}$	$(6.70 \pm 0.08) \times 10^{-5}$
2061	$(3.43 \pm 0.06) \times 10^{-13}$	$(5.7 \pm 0.9) \times 10^{-6}$
3911	$(2.26 \pm 0.07) \times 10^{-13}$	$< 2 \times 10^{-6}$























